



FORM PDP-1449 (Based on Form PTO-1449)

PATENT AND TRADEMARK OFFICE  
INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Sheet 1 of 1

ATTORNEY DOCKET No.

4041J-000499DVE

SERIAL No.

10/651,277

APPLICANT

Yoshifuma Okabe et al.

FILING DATE

08/28/2003

GROUP

To be assigned

## U.S. PATENT DOCUMENTS

Ref. Desig.	Examiner's Initials	Document Number	Date	Name	Class/ Subclass	(If appropriate) Filing Date
1.	Loke	3,858,238	12/1974	Nakamura et al.	257/591	
2.		3,879,230	04/1975	Nakamura et al.	257/607	
3.		4,751,191	06/1988	Gonsiorawski et al.	438/72	
4.		5,065,216	11/1991	Suzuki et al.	257/517	
5.		5,077,143	12/1991	Barraclough et al.	428/690	
6.	Loke	6,114,193	09/2000	Chang et al.	438/140	

## FOREIGN PATENT DOCUMENTS

Ref. Desig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Translation Yes	No
1.							

## OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)

Ref. Desig.	Examiner's Initials	
1.		

Examiner:

Loke

Date Considered:

9/19/04

EXAMINER: Please initial if citation considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>FORM HDP-1449 (Based on Form PTO-1449)</b>  <b>PATENT AND TRADEMARK OFFICE</b> <b>INFORMATION DISCLOSURE CITATION</b> (Use several sheets if necessary)  Sheet 1 of 3	ATTORNEY DOCKET NO.	SERIAL NO.
	4041J-000499DVE	To be assigned
	APPLICANT	
	Yoshifuma Okabe et al.	
	FILING DATE	GROUP
	Herewith	To be assigned

U.S. PATENT DOCUMENTS						
Ref. Desig.	Examiner's Initials	Document Number	Date	Name	Class/ Subclass	(If appropriate) Filing Date
1.	Loke	4,853,345	8/1989	Himelick		
2.		4,879,250	11/1989	Chan		
3.		4,859,629	8/1989	Reardon et al.		
4.		4,927,784	5/1990	Kazior et al.		
5.		4,931,412	6/1990	Fischer et al.		
6.		4,985,740	1/1991	Shenai et al.		
7.		5,241,862	9/1993	Okabe et a.		
8.		5,333,961	8/1994	Lidow et al.		
9.	Loke	5,689,130	11/1997	Okabe et al.	252/342	

FOREIGN PATENT DOCUMENTS							
Ref. Desig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Translation Yes No	
1.	Loke	57-15420	1/1982	JAPAN			
2.	Loke	58-45814	10/1993	JAPAN			
3.	Loke	59-113629	6/1985	JAPAN			
4.	Loke	59-189625	10/1984	JAPAN			
5.	Loke	59-213140	12/1984	JAPAN			
6.	Loke	59-220937 -	12/1994	JAPAN			
7.	Loke	61-234041 -	10/1986	JAPAN			
8.	Loke	61-296769 -	12/1986	JAPAN			
9.	Loke	62-23170 -	1/1987	JAPAN			

Examiner: <u>Loke</u>	Date Considered: <u>9/19/04</u>
-----------------------	---------------------------------

EXAMINER: Please initial if citation considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<p>FORM HDP-1449 (Based on Form PTO-1449)</p> <p><b>PATENT AND TRADEMARK OFFICE</b></p> <p><b>INFORMATION DISCLOSURE CITATION</b></p> <p>(Use several sheets if necessary)</p> <p>Sheet 2 of 3</p>	ATTORNEY DOCKET NO.	SERIAL NO.
	4041J-000499DVE	To be assigned
	APPLICANT	
	Yoshifuma Okabe et al.	
	FILING DATE	GROUP
Herewith	To be assigned	

FOREIGN PATENT DOCUMENTS							
Ref. Desig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Translation Yes	No
10.	Loke	62-43123	10/1987	JAPAN			
11.	Loke	62-243332	10/1987	JAPAN			
12.	Loke	62-293678	12/1987	JAPAN			
13.	Loke	63-253633	10/1988	JAPAN			
14.	Loke	1-169970	7/1989	JAPAN			
15.	Loke	57-097630	6/1982	JAPAN			

OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)		
Ref. Desig.	Examiner's Initials	
1.	Loke	KRISHINA SHENAI, "Vertical-Power DMOSFET", IEEE Elect. Device Letter, Vol. No. 10, No 3, 1989
2.	Loke	Krishnam Shenai, "Optimally Scaled Low-Voltage Vertical Power MOSFET's for High-Frequency Power Conversion", IEEE Trans. of Elect. Device Vol. 37 No. 4, 4/1990.
3.	Loke	C.Y. Ting et al., "The Use of Titanium-based Contact Barrier Layers in Silicon Technology", Thin Solid Films, 96(1982) 327-345 Electronics and Optics
4.	Loke	Semiconducotr Devices-Physics and Technology, Jan. 1985 S.M. Sze page 307
5.	Loke	Alvin B. Phillips, "Transistor Engineering and Introduction to Integrated Semiconductor Circuits", page 76
6.	Loke	S. Ogawa et al. "HRTEM and Nno-Scale Micro Analysis of Titanium/Silicon Interfacial Reaction Correlated With Electrical Properties, Extended Abstract.
7.	Loke	Wolf et al. "Silicon Processing For The VLSI Era, Vol. 1: Process Tech.", Lattice Press, 1986.

Examiner:	Loke	Date Considered:	9/19/04
-----------	------	------------------	---------

EXAMINER: Please initial if citation considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<p>FORM HDP-1449 (Based on Form PTO-1449)</p> <p><b>PATENT AND TRADEMARK OFFICE</b></p> <p><b>INFORMATION DISCLOSURE CITATION</b></p> <p>(Use several sheets if necessary)</p> <p>Sheet 3 of 3</p>	ATTORNEY DOCKET No.	SERIAL No.
	4041J-000499DVE	To be assigned
	APPLICANT	
	Yoshifuma Okabe et al.	
	FILING DATE	GROUP
Herewith	To be assigned	

OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)		
Ref. Desig.	Examiner's Initials	
8.	<i>Loke</i>	K. Shenai et al. "Characteristics of As-Deposited and Sintered Mo/LPCVD W Contacts to as, B, and P Doped Silicon", 1988 Materials Research Sociest, p. 219-224
9.	<i>Loke</i>	K. Shenai et al. "Blanket LPCVD Tungsten Silicide Technology for Smart Power Applications", IEEE Electron Device Letters, vol. 10, no 6 1989m p. 270-273.
10.	<i>Loke</i>	K. Shenai et al., "High-Performanc Vertical-Power DMOSFET's with Selectively Silicided Gate and Source Regions", IEEE Electron Device Letters, vol. 10, no. 4, 1989,p.153-155
11.	<i>Loke</i>	K. Shenai et al. "Selectively Silicided Vertical Power double-diffused metal-oxide semiconductor field effect transisotr for high-frequency power switching applications", J. Vac. Sci. Tehcnol. B6(6), 1988, p. 1740-1745.
12.	<i>Loke</i>	H.R. Chang et al. "Self-Aligned UMOSFET's with a Specific On-Resistance of , IEEE Transactions on Electron Devices, vol. ED-34, no. 11, 1987, p. 2329-2334
13.	<i>Loke</i>	K. Shenai et al. "Selectively Silicided Vertical Power DMOSFET's for High-Frequency Power Conversion" Electronics Letters, vol. 25 no. 12, 1989, p. 784-785.
14.	<i>Loke</i>	Webster's II New Riverside University Dictionary, 1984, P,549
15.	<i>Loke</i>	Semiconductot devices and technology, by S.M. Sze, P.38

Examiner:	<i>Loke</i>	Date Considered:	<i>9/19/04</i>
-----------	-------------	------------------	----------------

EXAMINER: Please initial if citation considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.